

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



2 DEC 2004



(43) International Publication Date
8 January 2004 (08.01.2004)

PCT

(10) International Publication Number
WO 2004/003261 A1

(51) International Patent Classification⁷: C30B 9/00, 29/40

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(21) International Application Number:

PCT/PL2003/000040

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(22) International Filing Date: 17 April 2003 (17.04.2003)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

P-354740 26 June 2002 (26.06.2002) PL
P-357697 11 December 2002 (11.12.2002) PL

(81) Designated States (*national*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

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(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: PROCESS FOR OBTAINING OF BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE

(57) Abstract: The invention relates to new improvements in a process for crystal growth in the environment of supercritical ammonia-containing solution, which are based on use of specific azide mineralizers and result in the improved bulk Group XIII element nitride monocrystals, in particular bulk monocrystalline gallium-containing nitride, intended mainly for variety of nitride-based semiconductor products such as various opto-electronic devices. The invention further relates to a mineralizer used for supercritical ammonia-containing solution which comprises at least one compound selected from the group consisting of LiN₃, NaN₃, KN₃, and CsN₃.

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